

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVV030A** is Designed for

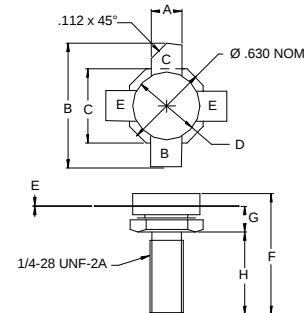
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	16 A
V_{CBO}	60 V
V_{CEO}	30 V
V_{EBO}	4.0 V
P_{DISS}	150 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.2 °C/W

PACKAGE STYLE .500 4L STUD(A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.050 / 26.67
C	.545 / 13.84	.555 / 14.10
D	.495 / 12.57	.505 / 12.83
E	.003 / 0.08	.007 / 0.18
F		.830 / 21.08
G	.185 / 4.70	.198 / 5.03
H	.497 / 12.62	.530 / 13.46

ORDER CODE: ASI10661

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 100 mA	60			V
BV_{CER}	I _C = 100 mA R _{BE} = 10 Ω	60			V
BV_{CEO}	I _C = 100 mA	30			V
BV_{EBO}	I _E = 10 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		120	---
C_{OB}	V _{CB} = 30 V f = 1.0 MHz			150	pF
P_G	V _{CE} = 28 V I _C = 3.5 A f = 225 MHz	7.5			dB
IMD₁	P _{OUT} = 30 W	-53			dBc